

Silicon PNP Power Transistors

2SA900

DESCRIPTION

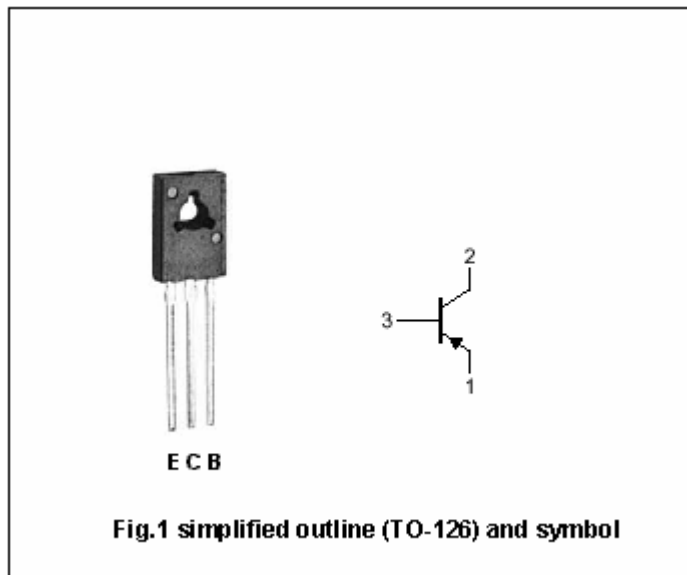
- With TO-126 package
- Complement to type 2SC1568
- Low collector saturation voltage

APPLICATIONS

- For audio frequency power amplifier

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

Absolute Maximun Ratings ($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-20	V
V_{CEO}	Collector-emitter voltage	Open base	-18	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-1	A
I_{CM}	Collector current-peak		-2	A
P_C	Collector power dissipation	$T_C=25^\circ\text{C}$	1.2	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=-1mA; I_B=0$	-18			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=-10\mu A; I_E=0$	-20			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=-10\mu A; I_C=0$	-5			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=-1A; I_B=-50mA$			-0.5	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=-500mA; I_B=-50mA$			-1.2	V
I_{CBO}	Collector cut-off current	$V_{CB}=-10V; I_E=0$			-1	μA
I_{CEO}	Collector cut-off current	$V_{CE}=-18V; I_B=0$			-10	μA
h_{FE-1}	DC current gain	$I_C=-500mA; V_{CE}=-2V$	90		470	
h_{FE-2}	DC current gain	$I_C=-1.5A; V_{CE}=-2V$	50			
C_{OB}	Output capacitance	$I_E=0; V_{CB}=-6V; f=1MHz$		40		pF
f_T	Transition frequency	$I_E=50mA; V_{CB}=-6V$		200		MHz

◆ h_{FE-1} Classifications

Q	R	S	T	U
90-155	130-210	180-280	250-360	330-470

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PACKAGE OUTLINE

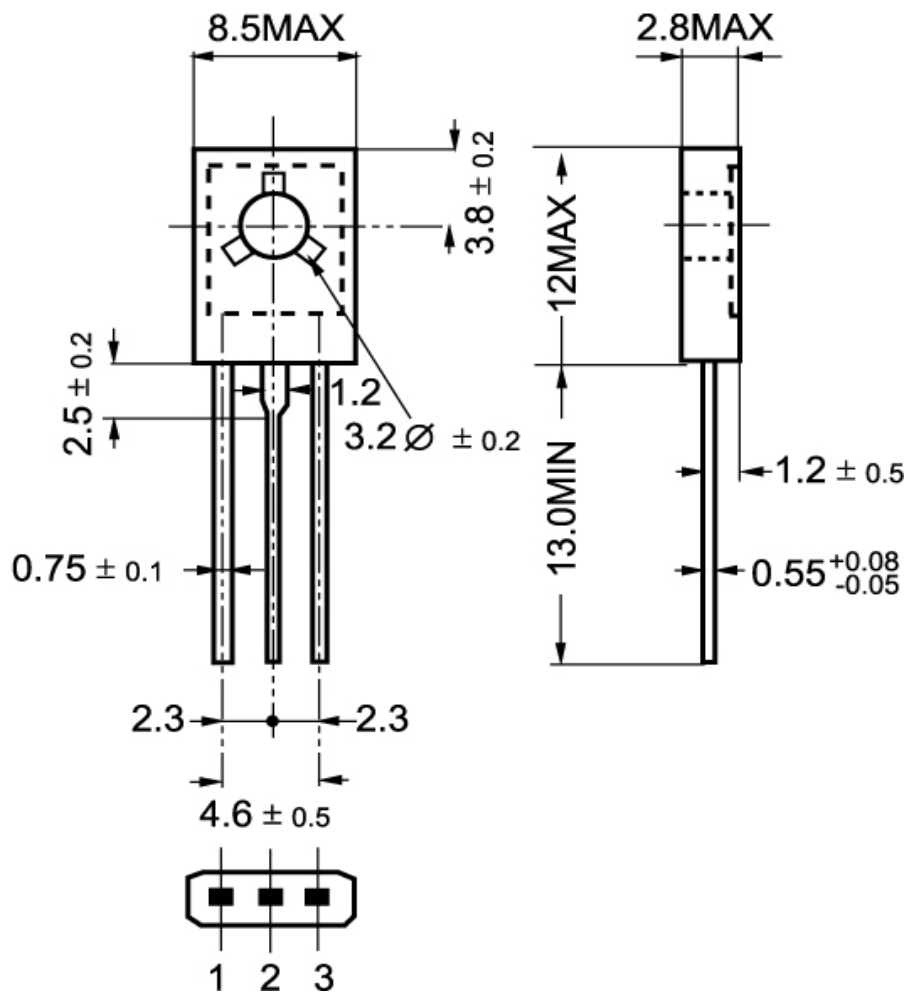


Fig.2 Outline dimensions